

Application No.: 09/851,324

Docket No.: 21776-00057-US

**In the Claims**

✓  
Please cancel claims 15-21 without prejudice or disclaimer as to the subject matter contained therein.

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**Please add the following new claims 22-26:**

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22. A method for fabricating a spherical semiconductor device having spherical bumps on surface electrodes of a spherical semiconductor element, the method comprising:  
temporarily arranging conductive balls for forming said spherical bumps on an arrangement substrate at positions respectively corresponding to said surface electrodes; and  
transferring said conductive balls onto said surface electrodes to join the electrodes,  
wherein said conductive balls are transferred from said arrangement substrate to said surface electrodes while the position of each of said conductive balls on said arrangement substrate is controlled,  
wherein said conductive balls are transferred from said arrangement substrate to said surface electrodes such that a desired gap is formed between a surface of said arrangement substrate and a surface of said spherical semiconductor element, and  
wherein said conductive balls are transferred onto and joined to said surface electrodes by thermo-compression bonding.

23. A method for fabricating a spherical semiconductor device having spherical bumps on surface electrodes of a spherical semiconductor element, the method comprising:  
temporarily arranging conductive balls for forming said spherical bumps on an arrangement substrate at positions respectively corresponding to said surface electrodes; and  
transferring said conductive balls onto said surface electrodes to join the electrodes,  
wherein said conductive balls are transferred from said arrangement substrate to said surface electrodes while the position of each of said conductive balls on said arrangement substrate is controlled,

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wherein said conductive balls are transferred from said arrangement substrate to said surface electrodes such that a desired gap is formed between a surface of said arrangement substrate and a surface of said spherical semiconductor element, and

wherein said conductive balls are transferred onto and joined to said surface electrodes by melting.

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(contd)*

24. The method according to claim 23, wherein each of said conductive balls are transferred onto and joined to each of said surface electrodes after at least one of the surface electrodes and conductive balls is coated with a flux.

25. The method according to claim 23, wherein conductive balls are arranged on said arrangement substrate to correspond to electrodes of spherical semiconductor elements, wherein said conductive balls are transferred onto said spherical semiconductor elements from said arrangement substrate to form corresponding bumps.

26. The method according to claim 22, wherein conductive balls are arranged on said arrangement substrate to correspond to electrodes of spherical semiconductor elements, wherein said conductive balls are transferred onto said spherical semiconductor elements from said arrangement substrate to form corresponding bumps.

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